

Enhancement and deterioration of the critical current by defects in Josephson-junction arrays

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We study how the addition of defects in an otherwise uniform Josephson junction array modifies the critical current of the array, by numerically solving the system of coupled Josephson equations. Our results confirm the existence of two different regimes, depending on the normalized maximum Josephson current of each junction, $i_{\max}$: for large $i_{\max}$, the defects deteriorate partially the critical state of the uniform array and so decrease the critical current, while for low values of $i_{\max}$, the defects help the formation of the critical state, which leads to an enhancement of critical current. The results are discussed in comparison with the behavior of type-II superconductors, for which the inclusion of defects always results in an enhancement of the critical current.

The traditional way of improving the critical current of hard type-II superconductors has been the introduction of defects, which act as pinning sites of the vortices. Based on the analogy between the magnetic properties of superconductors and Josephson junction (JJ) arrays, it seems reasonable to expect that in the latter system the presence of defects will yield to an improved total critical current. This has been the predominant point of view, starting from the work of Josephson himself [1]. His point of view was followed in later researches on defects containing JJ's [2–5], and in systematic works on planar JJ arrays, where Josephson vortices (JV's) and their depinning were studied (for example, see [6–12]). Moreover, it has become evident that one of the limiting factors for the critical current of actual high- T_c superconductors is the presence of a granular structure consisting of superconducting grains connected by JJ's. The role played by the defects in JJ arrays with respect to transport current is therefore a topic of practical importance as well. Clem introduced the JV pinning mechanism as the reason for the intergranular critical state (CS) [13]. In this work, we study this problem by numerically solving the equations describing the behavior of a JJ array in which defects are introduced. Our results will demonstrate that, in contrast with the case of type-II superconductors, the total critical current in the array decreases when adding defects, except in the regime of low Josephson current, for which the inclusion of defects may help the formation of a CS which does not originally appear in the uniform JJ array.

In order to avoid complicated demagnetizing effects, the studied JJ array consists of a number of infinitely long superconducting grains along the z axis. Its xy -plane cross-section forms an $N_x \times N_y$ square lattice of parameter a , each grain being centered at (i, j) , with $i = 1, 2, \dots, N_x$ and $j = 1, 2, \dots, N_y$. Every pair of nearest grains is weakly linked by a (when looking at it along the z axis) short JJ, which has a line density of the maximum DC Josephson current $I_{\max}$ (A/m) and a line specific

resistance R (Ωm), the line being along the z dimension. The capacitance effects are neglected for studying a slow process. Four nearest grains with an enclosed void form a square cell, the effective void area being A_v (m^2). We name the gauge-invariant phase differences (GIPD's) for JJ's along the x and y axes θ_{ij}^x and θ_{ij}^y , respectively.

When a transport current with line density I_{array} is uniformly applied in the x direction, or a field H is uniformly applied in the z direction, a set of differential equations for the $2N_x N_y - N_x - N_y$ GIPD's of all JJ's of the JJ array is built up based on the DC and AC Josephson equations and the Ampère and the Ohm laws as

$$\begin{aligned}
 \frac{d\theta_{ij}^x}{dt^*} &= -2\pi h_0 - \theta_{ij}^x + \theta_{i,j+1}^x + \theta_{ij}^y - \theta_{i+1,j}^y \\
 &\quad - 2\pi i_{\max} \sin \theta_{ij}^x \quad (1 \leq i \leq N_x - 1, j = 1), \\
 \frac{d\theta_{ij}^x}{dt^*} &= \theta_{i,j-1}^x - 2\theta_{ij}^x + \theta_{i,j+1}^x + \theta_{ij}^y - \theta_{i,j-1}^y + \theta_{i+1,j-1}^y \\
 &\quad - \theta_{i+1,j}^y - 2\pi i_{\max} \sin \theta_{ij}^x \\
 &\quad (1 \leq i \leq N_x - 1, 2 \leq j \leq N_y - 1), \\
 \frac{d\theta_{ij}^x}{dt^*} &= 2\pi h_{N_y} + \theta_{i,j-1}^x - \theta_{ij}^x - \theta_{i,j-1}^y + \theta_{i+1,j-1}^y \\
 &\quad - 2\pi i_{\max} \sin \theta_{ij}^x \quad (1 \leq i \leq N_x - 1, j = N_y), \\
 \frac{d\theta_{ij}^y}{dt^*} &= 2\pi h_j - \theta_{ij}^y + \theta_{i+1,j}^y + \theta_{ij}^x - \theta_{i,j+1}^x \\
 &\quad - 2\pi i_{\max} \sin \theta_{ij}^y \quad (i = 1, 1 \leq j \leq N_y - 1), \\
 \frac{d\theta_{ij}^y}{dt^*} &= \theta_{i-1,j}^y - 2\theta_{ij}^y + \theta_{i+1,j}^y + \theta_{ij}^x - \theta_{i-1,j}^x + \theta_{i-1,j+1}^x \\
 &\quad - \theta_{i,j+1}^x - 2\pi i_{\max} \sin \theta_{ij}^y \\
 &\quad (2 \leq i \leq N_x - 1, 1 \leq j \leq N_y - 1), \\
 \frac{d\theta_{ij}^y}{dt^*} &= -2\pi h_j + \theta_{i-1,j}^y - \theta_{ij}^y - \theta_{i-1,j}^x + \theta_{i-1,j+1}^x \\
 &\quad - 2\pi i_{\max} \sin \theta_{ij}^y \\
 &\quad (i = N_x, 1 \leq j \leq N_y - 1). \tag{1}
 \end{aligned}$$

In these equations, t^* is the normalized time t to the nominal time constant τ of one cell, $t^* = t/\tau = tR/\mu_0 A_v$, and h_j and $i_{\max}$ are the boundary field H_j and $I_{\max}$ normalized to $\Phi_0/\mu_0 A_v$. Correspondingly, the normalization of I_{array} into i_{array} can be made in the same way as $I_{\max}$. We have $h_j = (j/N_y - 1/2)i_{\text{array}}$ in the transport case and $h_j = h$ in the magnetic case. The field H_{ij} in the (i, j) void (i and j are defined as those for the left-and-down adjacent grain) produced by DC Josephson currents normalized to $\Phi_0/\mu_0 A_v$ is calculated by

$$h_{ij} = (\theta_{ij}^y - \theta_{i+1,j}^y + \theta_{i,j+1}^x - \theta_{ij}^x)/2\pi, \quad (2)$$

where we have assumed the phase of the order parameter to be zero in each grain.

It is known [14,15] that a uniform slablike JJ array [16] can be in the CS when $i_{\max}$ is large enough, while for lower values of $i_{\max}$ it presents a JV state. Such an evolution in 1D JJ array from the JV state to the CS has been studied mathematically by Greene in terms of a standard mapping technique. His conclusion is that a stochastic transition occurs at $i_{\max} = i_{\max}^* = 0.9716 \dots / 2\pi \approx 0.155$ [14,15].

The transition from a JV state to a CS occurs in our (mathematically 2D) JJ array as well. To show this transition, we analyze the field profiles in a JJ array of $N_x = N_y = 25$ in the saturated remanence state. The profiles are calculated using a Runge-Kutta method as follows. We start from $\{\theta_{ij}^{x,y} = 0\}$, step h from 0 to 100 and calculate the fully relaxed $\{h_{ij}\}$, and then step h down to 0 and calculate again the fully relaxed $\{h_{ij}\}$, which is our solution.

As seen in Fig. 1, the profiles of uniform JJ arrays with $i_{\max} = 0.01, 0.05$, and 0.1 show JV states with 8, 24, and 64 JV's of roughly equal heights. For $i_{\max} = 0.17$, there is a central peak remarkably higher than the others, indicating a transition from the JV state to the CS. When $i_{\max} \geq 0.4$, the entire profile appears to be a single peak of pyramid shape (as shown in the figure for $i_{\max} = 1$), which is the distinctive characteristic of the Bean CS, as in hard superconductors, where the penetrated supercurrents flow with a density J equal to the critical-current density J_c [17].

Let us now study the effect of introducing defects in the array by changing $i_{\max}$ of JJ's connecting certain defect grains into $i_{\max,d} = ci_{\max}$, where $0 < c \neq 1$. First we consider the case for low values of $i_{\max}$, for which the uniform JJ array does not show a CS. In order to be able to check the validity of the solutions by their symmetry, we choose symmetrically and uniformly distributed defects shown in Fig. 2(a) with $c = 0.1$. The trend observed in the calculated results shown in Fig. 1 is clear: defects help the formation of the CS. For the nonuniform JJ array of $i_{\max} = 0.01$, there is a 12-peak structure with eight outer peaks lower than the inner four. When $i_{\max}$ is increased to 0.05 , the profile appears to be a single round peak, indicating a transition from the JV state to the CS. The profiles for $i_{\max} = 0.1$ and 0.17 are already

of an overall pyramid shape, typical for the Bean CS, in clear contrast to the results for the uniform JJ array. We confirm therefore that the inclusion of defects in the array with low values of $i_{\max}$ results in the enhancement and even induction of the CS.

After this conclusion, an important question arises as: Is this behavior general for all values of $i_{\max}$? The previous result of the decreasing of the trapped flux for $i_{\max} = 1$ [as seen in Fig. 1(i)] already gives us a hint of the actual striking behavior: for such values of $i_{\max}$ that the uniform array develops a good CS, the addition of defects results in a decrease of critical current.

To further confirm the above statement we set two square defect clusters shown in Fig. 2(b). Our aim is to calculate the line density of the critical current of the JJ array, $i_{c,\text{array}}$, namely, the maximum i_{array} at which a static solution can be obtained. The reference is chosen as the uniform ($c = 1$) JJ array of $i_{\max} = 1$. We start from a zero-field cooled state at $t^* = 0$ with $\{\theta_{ij}^{x,y} = 0\}$, and change i_{array} between 0 and 25 (the maximum possible value for $i_{\max} = 1$) to calculate the fully relaxed GIPD's that corresponds to $i_{c,\text{array}}$.

The calculated $i_{c,\text{array}}$ as a function of c is given in Fig. 3. We can see that the presence of defects makes $i_{c,\text{array}}$ smaller in general. It equals 24 when $0.995 \leq c \leq 1.519$, and decreases stepwise if c is out of this range. The reasons for this are twofold. (i) Since i_{array} flows in the horizontal x direction through JJ's of $i = 1$ to 25 in series, it is limited by the ideal critical current $i_{c,\text{array,ideal}}$ defined as the smallest sum of $i_{\max}$ and $i_{\max,d}$ of all the horizontal JJ's for each i th vertical cross-section. For the array in Fig. 2(b), $i_{c,\text{array,ideal}} = 25$ if $c \geq 1$ and $i_{c,\text{array,ideal}} = 19 + 6c$ if $c < 1$. (ii) The phase coupling related to Eq. (2) makes $i_{c,\text{array}} < i_{c,\text{array,ideal}}$, so that the calculated $i_{c,\text{array}} < 25$ if $c \geq 1$ and $i_{c,\text{array}} < 19 + 6c$ if $c < 1$. The effect of the defects on the critical current of the nonuniform array can be observed in greater detail from the calculated current distributions in the array for different values of c presented in [18].

To sum up, we have shown that the addition of defects in a JJ array helps to settle a CS in the system if the normalized JJ current $i_{\max}$ is small. However if $i_{\max}$ is large enough, that is for the cases in which the uniform array is in a good CS, the introduction of defects deteriorate the critical current of the array. The latter feature is in contrast with the popular view that the CS arises from JV pinning. From these results, it is imperative to conclude that the origin of the CS in JJ arrays is a phenomenon more complex than a JV pinning analogous to the Abrikosov vortex pinning in hard type-II superconductors.

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FIG. 1. Trapped field profiles of 25×25 square-columnar JJ arrays at saturated remanence. (a), (c), (e), (g), and (i) are for uniform JJ arrays; (b), (d), (f), (h), and (j) are for nonuniform JJ arrays with $i_{\max,d} = i_{\max}/10$. Relative h scale factors $1/i_{\max}$ are used.

FIG. 2. The xy cross-section of the studied JJ arrays. The defect grains are marked by shadow. (a) and (b) are chosen for the cases of small and large values of $i_{\max}$, respectively.

FIG. 3. The JJ critical current $i_{c,array}$ as a function of c .

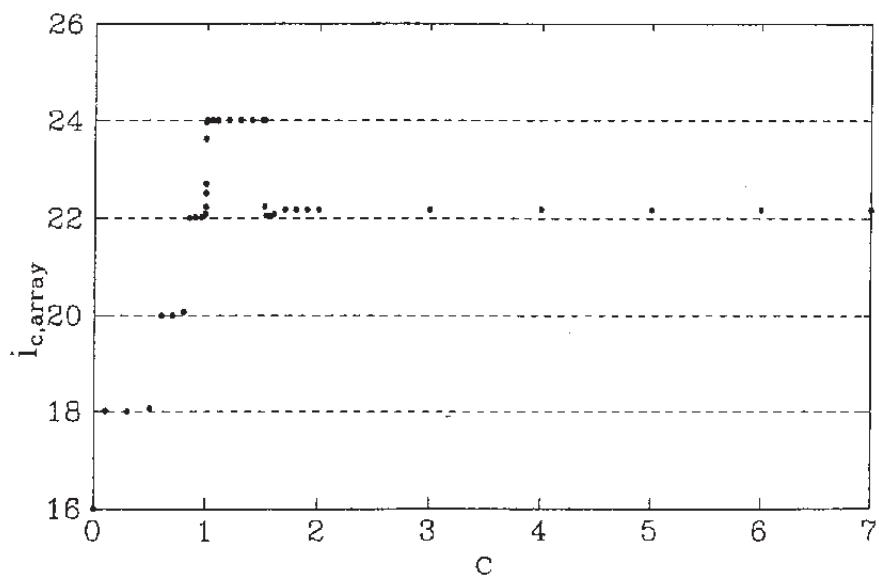
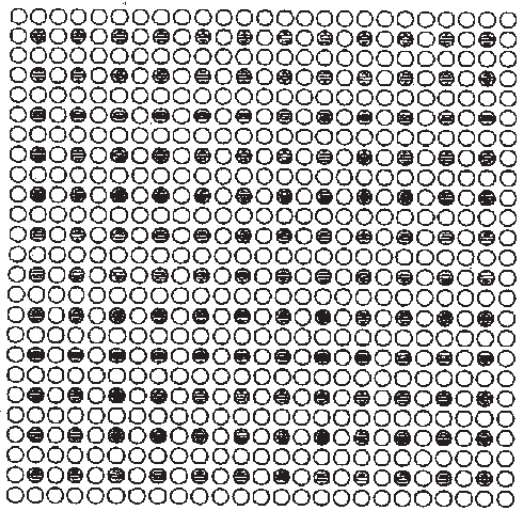
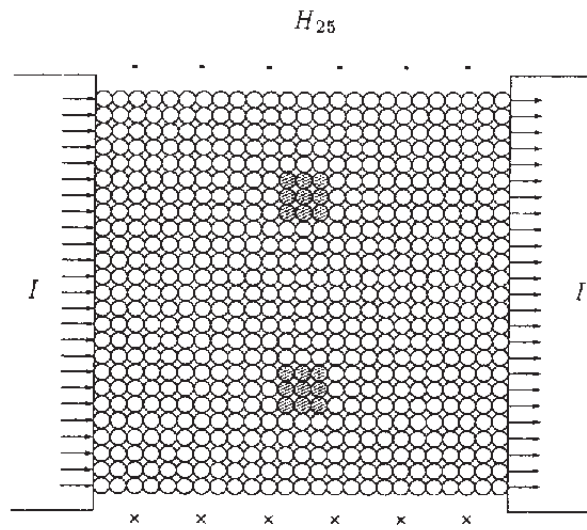


Fig 3



(a)

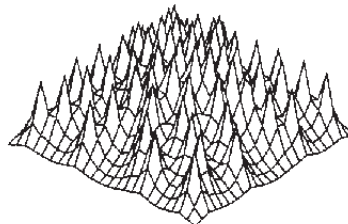


(b)

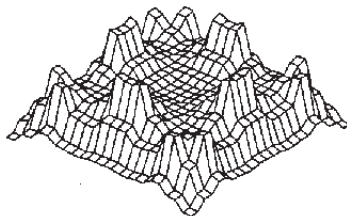
Fig 1



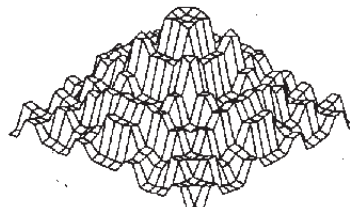
(a) $i_{max}=0.01$, uniform



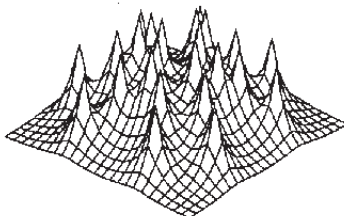
(e) $i_{max}=0.1$, uniform



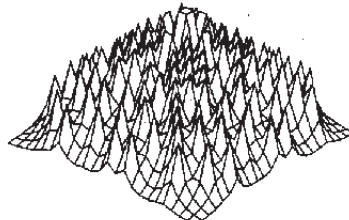
(b) $i_{max}=0.01$, nonuniform



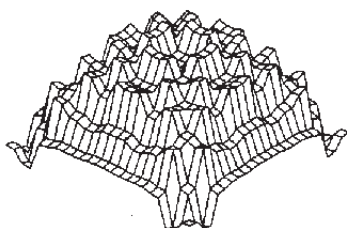
(f) $i_{max}=0.1$, nonuniform



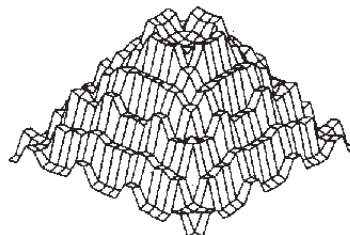
(c) $i_{max}=0.05$, uniform



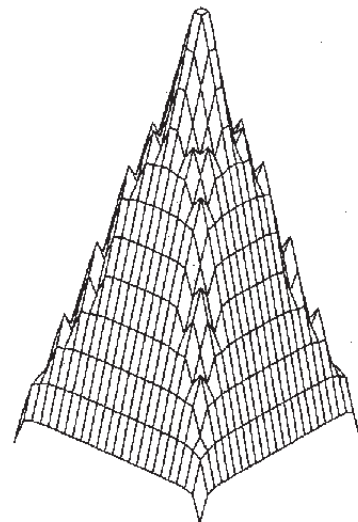
(g) $i_{max}=0.17$, uniform



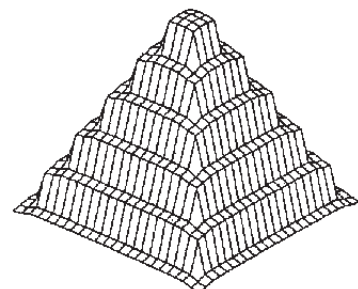
(d) $i_{max}=0.05$, nonuniform



(h) $i_{max}=0.17$, nonuniform



(i) $i_{max}=1$, uniform



(j) $i_{max}=1$, nonuniform

Fig 2